

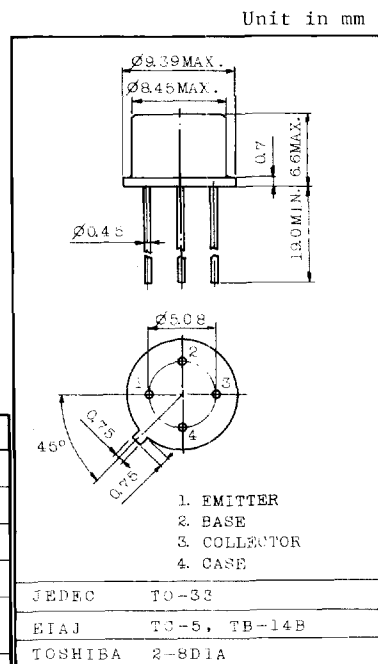
HIGH FREQUENCY WIDE BAND AMPLIFIER APPLICATIONS.
HIGH FREQUENCY LOW NOISE AMPLIFIER APPLICATIONS.

FEATURES:

- Low Noise for High and Low Frequency
 - : NF=4.0dB (Max.) f=200MHz
 - : NF=11dB (Max.) f=10kHz

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	35	V
Emitter-Base Voltage	V _{EB0}	3	V
Collector Current	I _C	300	mA
Collector Power Dissipation	P _C	600	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-65 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} =20V, I _E =0	-	-	0.1	μA
Collector-Base Breakdown Voltage	V(BR)CBO	I _C =0.1mA, I _E =0	50	-	-	V
Collector-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, I _B =0	35	-	-	V
Emitter-Base Breakdown Voltage	V(BR)EBO	I _E =0.1mA, I _C =0	3	-	-	V
DC Current Gain	h _{FE}	V _{CE} =10V, I _C =20mA	40	80	200	-
Transition Frequency	f _T	V _{CE} =10V, I _E =-20mA	1000	1400	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =15V, I _E =0, f=1MHz	-	2.2	3.0	pF
Noise Figure	NF(1)	V _{CE} =10V, I _E =-10mA, R _g =50Ω, f=200MHz	-	2.5	4.0	dB
	NF(2)	V _{CE} =15V, I _E =-30mA, R _g =500Ω, f=10kHz	-	6	11	dB

